

60 V, N-channel Trench MOSFET

11 January 2024

**Product data sheet** 

## 1. General description

N-channel enhancement mode Field-Effect Transistor (FET) in a small SOT23 Surface-Mounted Device (SMD) plastic package using Trench MOSFET technology.

## 2. Features and benefits

- Logic-level compatible
- Extended temperature range T<sub>i</sub> = 175 °C
- Trench MOSFET technology
- ElectroStatic Discharge (ESD) protection
- AEC-Q101 qualified

## 3. Applications

- Relay driver
- High-speed line driver
- Low-side load switch
- Switching circuits

## 4. Quick reference data

#### Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
V <sub>DS</sub>	drain-source voltage	T <sub>j</sub> = 25 °C		-	-	60	V
V <sub>GS</sub>	gate-source voltage			-20	-	20	V
I <sub>D</sub>	drain current	V <sub>GS</sub> = 10 V; T <sub>amb</sub> = 25 °C	[1]	-	-	250	mA
Static chara	cteristics						
R <sub>DSon</sub>	drain-source on-state resistance	V <sub>GS</sub> = 10 V; I <sub>D</sub> = 100 mA; T <sub>j</sub> = 25 °C		-	2.2	3	Ω

[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for drain 1 cm<sup>2</sup>.



# 5. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	G	gate		D
2	S	source		
3	D	drain		G G S 017aaa255

# 6. Ordering information

Table 3. Ordering information						
Type number	Package					
	Name	Description	Version			
BSS138AK-Q	SOT23	plastic, surface-mounted package; 3 terminals; 1.9 mm pitch; 2.9 mm x 1.3 mm x 1 mm body	SOT23			

# 7. Marking

### Table 4. Marking codes

Type number	Marking code[1]
BSS138AK-Q	J5%

[1] % = placeholder for manufacturing site code

60 V, N-channel Trench MOSFET

## 8. Limiting values

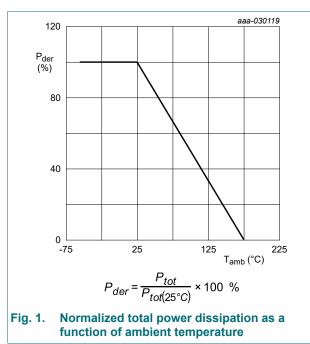
#### Table 5. Limiting values

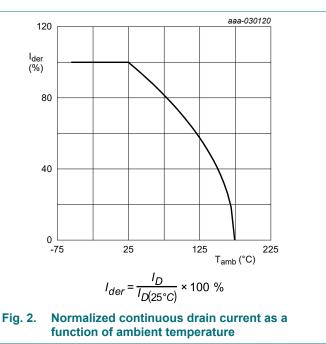
In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V <sub>DS</sub>	drain-source voltage	T <sub>j</sub> = 25 °C		-	60	V
V <sub>GS</sub>	gate-source voltage			-20	20	V
I <sub>D</sub>	drain current	V <sub>GS</sub> = 10 V; T <sub>amb</sub> = 25 °C	[1]	-	250	mA
		V <sub>GS</sub> = 10 V; T <sub>amb</sub> = 100 °C	[1]	-	180	mA
I <sub>DM</sub>	peak drain current	$T_{amb}$ = 25 °C; single pulse; $t_p \le 10 \ \mu s$		-	2	A
P <sub>tot</sub>	total power dissipation	T <sub>amb</sub> = 25 °C	[2]	-	320	mW
			[1]	-	390	mW
		T <sub>sp</sub> = 25 °C		-	1.6	W
Tj	junction temperature			-55	175	°C
T <sub>amb</sub>	ambient temperature			-55	175	°C
T <sub>stg</sub>	storage temperature			-65	175	°C
Source-drai	n diode					
Is	source current	T <sub>amb</sub> = 25 °C	[1]	-	250	mA
ESD maxim	um rating					
V <sub>ESD</sub>	electrostatic discharge voltage	НВМ		-	500	V
Avalanche r	uggedness			1		
E <sub>DS(AL)S</sub>	non-repetitive drain- source avalanche energy	T <sub>j(init)</sub> = 25 °C; I <sub>D</sub> = 20 mA; DUT in v avalanche (unclamped)		-	6.6	mJ

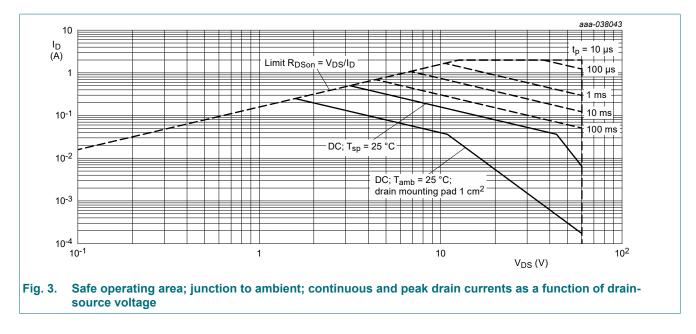
[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for drain 1 cm<sup>2</sup>.

[2] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.





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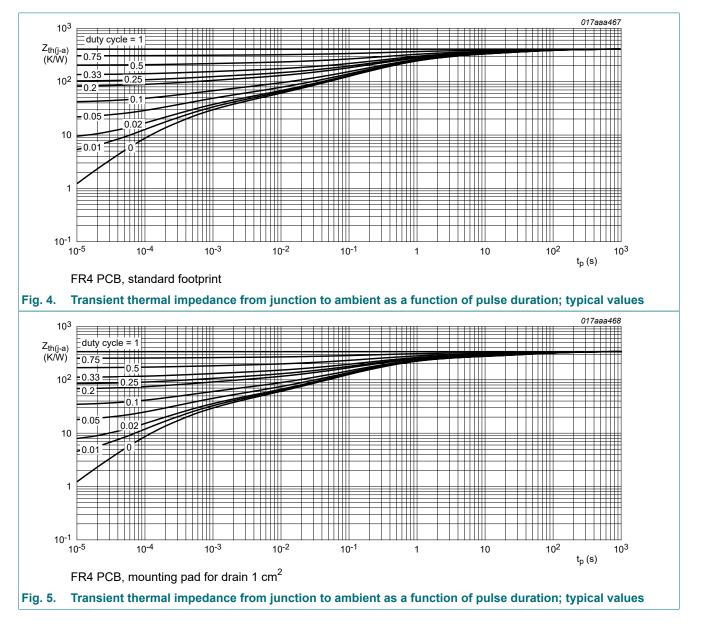


## 9. Thermal characteristics

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
R <sub>th(j-a)</sub> thermal resistance from junction to ambient	in free air	[1]	-	410	470	K/W	
		[2]	-	330	380	K/W	
R <sub>th(j-sp)</sub>	thermal resistance from junction to solder point			-	80	95	K/W

[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

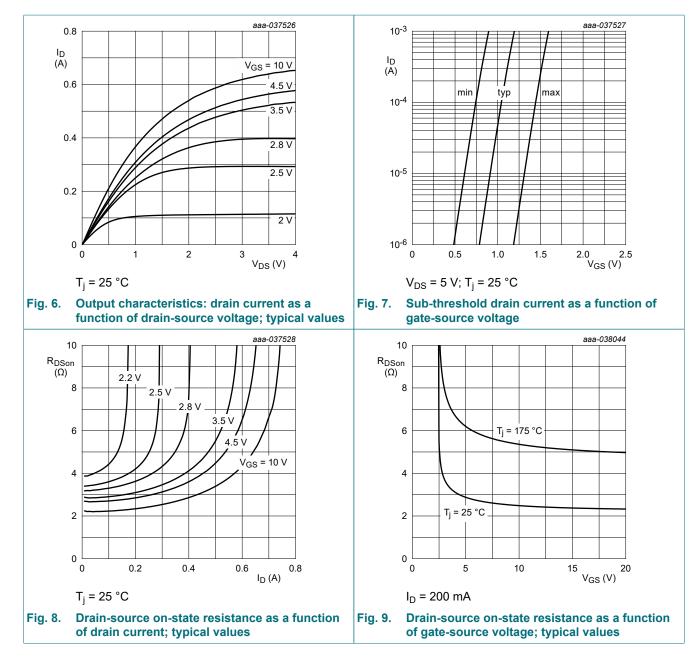
[2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for drain 1 cm<sup>2</sup>.



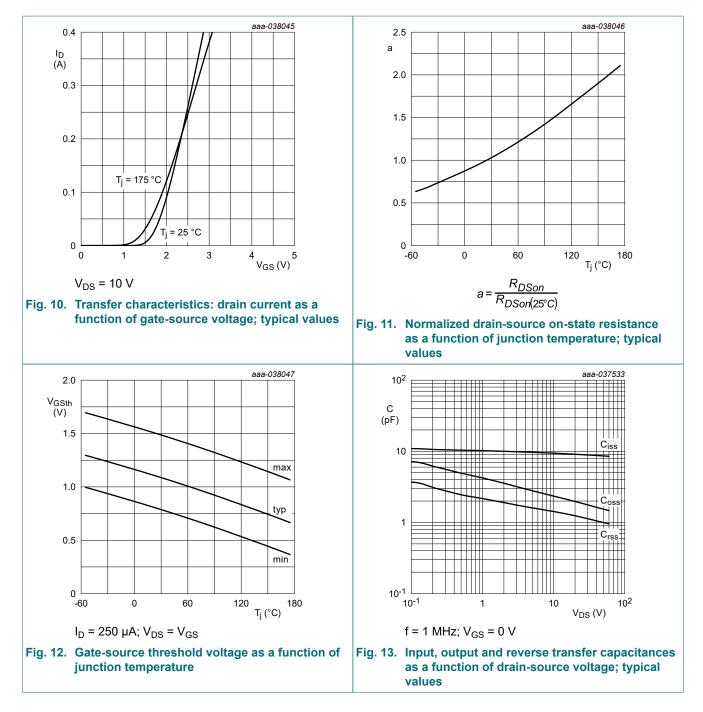
# **10. Characteristics**

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static chara	acteristics					
V <sub>(BR)DSS</sub>	drain-source breakdown voltage	$I_D$ = 250 µA; $V_{GS}$ = 0 V; $T_j$ = 25 °C	60	-	-	V
V <sub>GSth</sub>	gate-source threshold voltage	I <sub>D</sub> = 250 μA; V <sub>DS</sub> = V <sub>GS</sub> ; T <sub>j</sub> = 25 °C	0.8	1.1	1.5	V
I <sub>DSS</sub>	drain leakage current	V <sub>DS</sub> = 60 V; V <sub>GS</sub> = 0 V; T <sub>j</sub> = 25 °C	-	-	500	nA
		V <sub>DS</sub> = 60 V; V <sub>GS</sub> = 0 V; T <sub>j</sub> = 125 °C	-	-	5	μA
I <sub>GSS</sub>	gate leakage current	V <sub>GS</sub> = 20 V; V <sub>DS</sub> = 0 V; T <sub>j</sub> = 25 °C	-	-	10	μA
		V <sub>GS</sub> = -20 V; V <sub>DS</sub> = 0 V; T <sub>j</sub> = 25 °C	-	-	-10	μA
		V <sub>GS</sub> = 10 V; V <sub>DS</sub> = 0 V; T <sub>j</sub> = 25 °C	-	-	1	μA
		V <sub>GS</sub> = -10 V; V <sub>DS</sub> = 0 V; T <sub>j</sub> = 25 °C	-	-	-1	μA
		V <sub>GS</sub> = 4.5 V; V <sub>DS</sub> = 0 V; T <sub>j</sub> = 25 °C	-	-	500	nA
		$V_{GS}$ = -4.5 V; $V_{DS}$ = 0 V; $T_j$ = 25 °C	-	-	-500	nA
R <sub>DSon</sub>	drain-source on-state resistance	V <sub>GS</sub> = 10 V; I <sub>D</sub> = 100 mA; T <sub>j</sub> = 25 °C	-	2.2	3	Ω
		V <sub>GS</sub> = 10 V; I <sub>D</sub> = 100 mA; T <sub>j</sub> = 175 °C	-	4.6	6.3	Ω
		V <sub>GS</sub> = 4.5 V; I <sub>D</sub> = 50 mA; T <sub>j</sub> = 25 °C	-	2.7	3.9	Ω
		V <sub>GS</sub> = 2.5 V; I <sub>D</sub> = 10 mA; T <sub>j</sub> = 25 °C	-	3.4	12	Ω
9 <sub>fs</sub>	forward transconductance	V <sub>DS</sub> = 5 V; I <sub>D</sub> = 100 mA; T <sub>j</sub> = 25 °C	-	0.3	-	S
Dynamic ch	naracteristics		I			
Q <sub>G(tot)</sub>	total gate charge	$V_{DS}$ = 30 V; I <sub>D</sub> = 100 mA; V <sub>GS</sub> = 10 V;	-	0.21	0.315	nC
Q <sub>GS</sub>	gate-source charge	T <sub>j</sub> = 25 °C	-	0.022	-	nC
Q <sub>GD</sub>	gate-drain charge		-	0.051	-	nC
C <sub>iss</sub>	input capacitance	V <sub>DS</sub> = 30 V; f = 1 MHz; V <sub>GS</sub> = 0 V;	-	9	-	pF
C <sub>oss</sub>	output capacitance	T <sub>j</sub> = 25 °C	-	1.8	-	pF
C <sub>rss</sub>	reverse transfer capacitance		-	1.1	-	pF
t <sub>d(on)</sub>	turn-on delay time	$V_{DS}$ = 30 V; I <sub>D</sub> = 100 mA; V <sub>GS</sub> = 10 V;	-	1	-	ns
t <sub>r</sub>	rise time	R <sub>G(ext)</sub> = 6 Ω; T <sub>j</sub> = 25 °C	-	1	-	ns
t <sub>d(off)</sub>	turn-off delay time	1	-	2	-	ns
t <sub>f</sub>	fall time	1	-	3	-	ns
Source-drai	in diode	· ·	1			
V <sub>SD</sub>	source-drain voltage	I <sub>S</sub> = 250 mA; V <sub>GS</sub> = 0 V; T <sub>j</sub> = 25 °C	-	1	1.7	V
t <sub>rr</sub>	reverse recovery time	I <sub>S</sub> = 250 mA; dI <sub>S</sub> /dt = -100 A/μs;	-	7	-	ns
Qr	recovered charge	V <sub>GS</sub> = 0 V; V <sub>DS</sub> = 30 V; T <sub>j</sub> = 25 °C	-	1	-	nC

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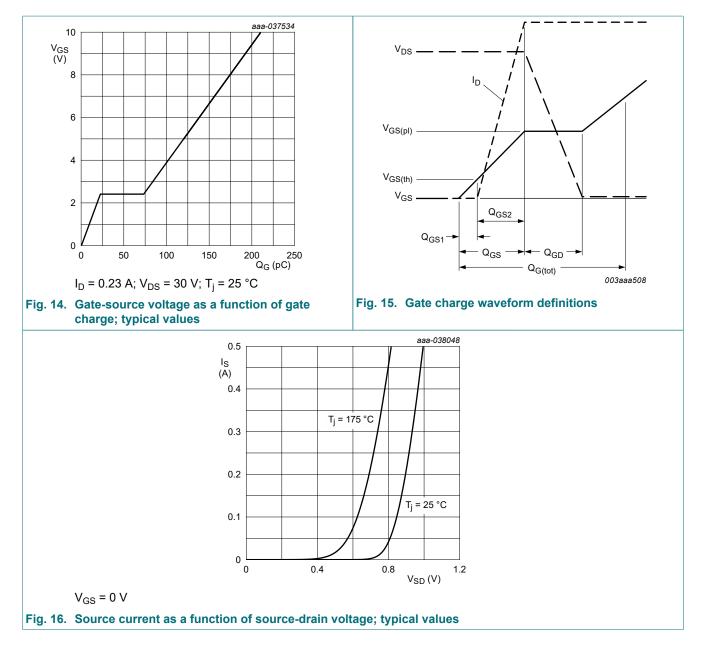


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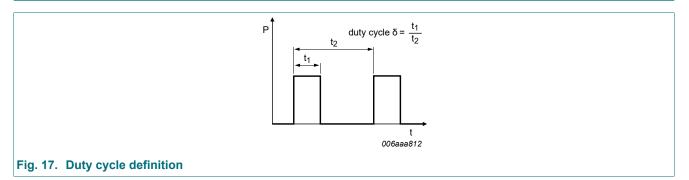


**Product data sheet** 

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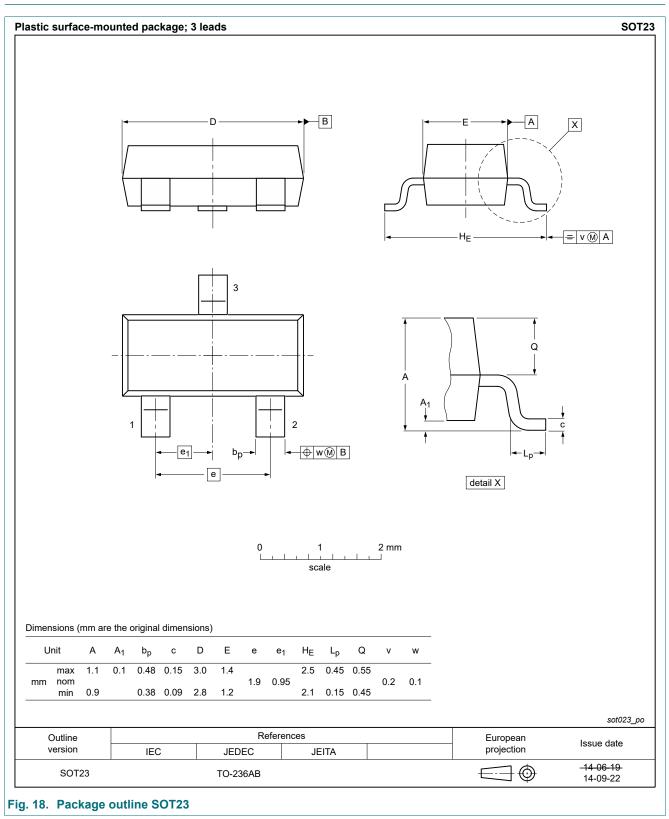
## **11. Test information**



### **Quality information**

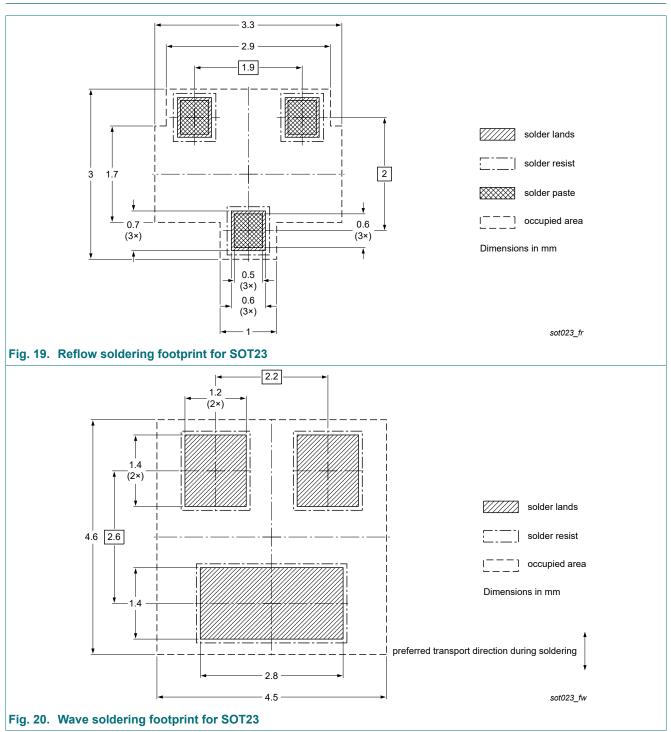
This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard *Q101* - *Stress test qualification for discrete semiconductors*, and is suitable for use in automotive applications.

## 12. Package outline



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## 13. Soldering



# 14. Revision history

Table 8. Revision history						
Data sheet ID	Release date	Data sheet status	Change notice	Supersedes		
BSS138AK-Q v.1	20240111	Product data sheet	-	-		

BSS138AK-Q

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# 15. Legal information

#### **Data sheet status**

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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